Signetics

82S23B, 82S123B
256-Bit TTL Bipolar PROM

Military Bipolar Memory Products

Product Specification

DESCRIPTION

The 82S23B and 82S123B are field-programmable, which means that custom patterns are immediately available by following the Signetics Generic I fusing procedure. The 82S23B and 82S123B devices are supplied with all outputs at a logical Low. Outputs are programmed to a logic High level at any specified address by fusing the Ni-Cr link matrix.

These devices include on-chip decoding and 1 chip enable input for memory expansion. They feature either Open collector or 3-State outputs for optimization of word expansion in bused organizations.

FEATURES

- **Address access time: 30ns max**
- **Input loading: -150μA max**
- **On-chip address decoding**
- **One chip enable input**
- **Output options:**
  - **82S23B: Open collector**
  - **82S123B: 3-State**
- **No separate fusing pins**
- **Unprogrammed outputs are Low level**
- **Fully TTL compatible**

APPLICATIONS

- **Prototyping/volume production**
- **Sequential controllers**
- **Format conversion**
- **Hardwired algorithms**
- **Random logic**
- **Code conversion**

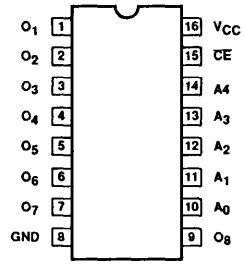
ORDERING INFORMATION

DESCRIPTION	ORDER CODE
16-Pin Ceramic Dual-In-Line 300mil-wide	82S23B/BEA, 82S123B/BEA
16-Pin Ceramic FlatPack	82S23B/BFA, 82S123B/BFA

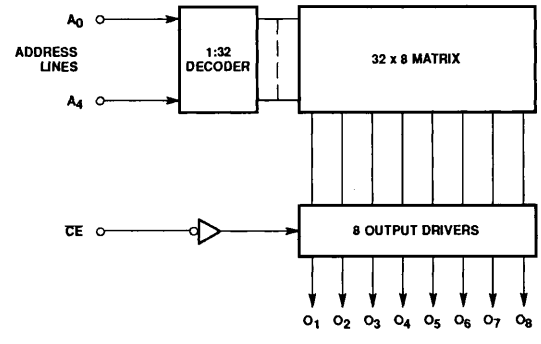
ABSOLUTE MAXIMUM RATINGS

SYMBOL	PARAMETER	RATING	UNIT
V_{CC}	Supply voltage	+7	V_{DC}
V_I	Input voltage	+5.5	V_{DC}
V_O	Output voltage High (82S23)	+5.5	V_{DC}
V_O	Output voltage Off-State (82S123)	+5.5	V_{DC}
T_A	Operating temperature range	-55 to +125	°C
T_{STG}	Storage temperature range	-65 to +150	°C

PIN CONFIGURATION



BLOCK DIAGRAM



256-Bit TTL Bipolar PROM (32 × 8) — 82S23B, 82S123B

DC ELECTRICAL CHARACTERISTICS -55°C ≤ T_A ≤ +125°C, 4.5V ≤ V_{CC} ≤ 5.5V

SYMBOL	PARAMETER	TEST CONDITIONS[1,2]	LIMITS			UNIT
			Min	Typ[5]	Max	
Input voltage						
V_{IL}[7]	Low				0.8	V
V_{IH}[7]	High		2.0			V
V_{IK}	Clamp	V_{CC} = 4.5V, I_I = -18mA			-1.2	V
Output voltage						
		$\overline{CE}$ = Low				
V_{OL}	Low	I_O = 16mA			0.5	V
V_{OH}	High (82S123B)	V_{CC} = 4.5V, I_O = -2mA	2.4			V
Input current						
		V_{CC} = 5.5V				
I_{IL}	Low	V_I = 0.45V			-150	µA
I_{IH1}	High	V_I = 2.7V			25	µA
I_{IH2}	High	V_I = 5.5V			40	µA
Output current						
		V_{CC} = 5.5V				
I_{OLK}	Leakage (82S23B)	$\overline{CE}$ = High, V_O = 5.5V			40	µA
I_{OZ}	Hi-Z state (82S123B)	$\overline{CE}$ = High, V_O = 5.5V			40	µA
		$\overline{CE}$ = High, V_O = 0.4V			-40	µA
I_{OS}	Short circuit (82S123B)[3]	V_{CC} = 5.5V, $\overline{CE}$ = Low, V_O = 0V, High stored	-20		-100	mA
Supply current						
I_{CC}		$\overline{CE}$ = High, V_{CC} = 5.5V			96	mA
Capacitance[6]						
		$\overline{CE}$ = High, V_{CC} = 5.0V				
C_{IN}	Input	V_I = 2.0V		5	10	pF
C_{OUT}	Output	V_O = 2.0V		8	13	pF

AC ELECTRICAL CHARACTERISTICS -55°C ≤ T_A ≤ +125°C, 4.5V ≤ V_{CC} ≤ 5.5V

SYMBOL	PARAMETER	TO	FROM	LIMITS			UNIT
				Min	Typ[5]	Max	
t_{AA}	Access time[4]	Output	Address		20	30	ns
t_{CE}	Access time[4]	Output	Chip Enable			18	ns
t_{CD}	Disable time	Output	Chip Disable			18	ns

NOTES:
1. Positive current is defined as into the terminal referenced.
2. All voltages with respect to network ground.
3. Duration of short circuit should not exceed 1 second.
4. Tested at an address cycle time of 1µs.
5. Typical values are at V_{CC} = 5V, T_A = +25°C.
6. Guaranteed but not tested.
7. These are absolute voltages with respect to device ground pin and include all overshoots due to system and/or tester noise. Testing of these values requires special equipment.

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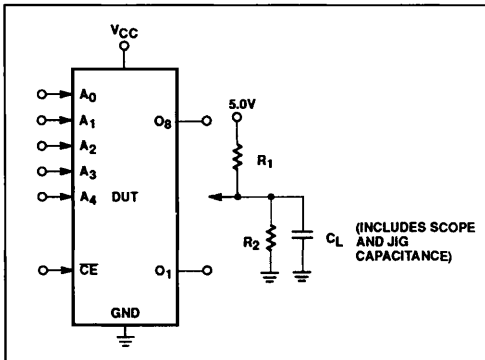
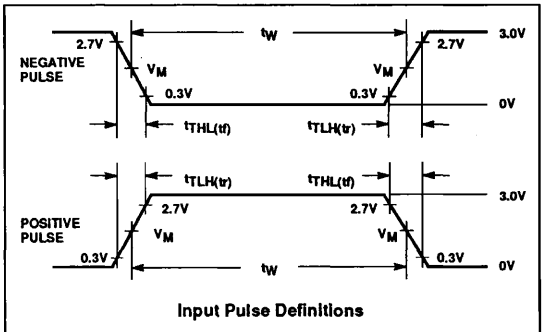
TEST LOAD CIRCUITS



NOTE:
R_1 = 270 Ω, R_2 = 600Ω, C_L = 50pF.

VOLTAGE WAVEFORMS



Input Pulse Definitions

INPUT PULSE CHARACTERISTICS				
V_M	Rep. Rate	Pulse Width	t_{TLH}	t_{THL}
1.5V	1MHz	500ns	≤5ns	≤5ns

TIMING DIAGRAMS